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AMD Xilinx - XC2S30-5CS144C Datasheet



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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	216
Number of Logic Elements/Cells	972
Total RAM Bits	24576
Number of I/O	92
Number of Gates	30000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-TFBGA, CSPBGA
Supplier Device Package	144-LCSBGA (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc2s30-5cs144c

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Ordering Information

Spartan-II devices are available in both standard and Pb-free packaging options for all device/package combinations. The Pb-free packages include a special "G" character in the ordering code.

Standard Packaging



Device Ordering Options

Device		Speed Grade		Number of Pins / Package Type		Temperatur	e Range (T _J)	
XC2S15	-5	Standard Performance	`	VQ(G)100	100-pin Plastic Very Thin QFP		C = Commercial	0°C to +85°C
XC2S30	-6	Higher Performance ⁽¹⁾	(CS(G)144	144-ball Chip-Scale BGA		I = Industrial	-40°C to +100°C
XC2S50			-	TQ(G)144	144-pin Plastic Thin QFP			
XC2S100			F	PQ(G)208	208-pin Plastic QFP			
XC2S150			F	FG(G)256	256-ball Fine Pitch BGA			
XC2S200			F	FG(G)456	456-ball Fine Pitch BGA			

Notes:

1. The -6 speed grade is exclusively available in the Commercial temperature range.

Device Part Marking



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Similarly, the F6 multiplexer combines the outputs of all four function generators in the CLB by selecting one of the F5-multiplexer outputs. This permits the implementation of any 6-input function, an 8:1 multiplexer, or selected functions of up to 19 inputs.

Each CLB has four direct feedthrough paths, one per LC. These paths provide extra data input lines or additional local routing that does not consume logic resources.

Arithmetic Logic

Dedicated carry logic provides capability for high-speed arithmetic functions. The Spartan-II FPGA CLB supports two separate carry chains, one per slice. The height of the carry chains is two bits per CLB.

The arithmetic logic includes an XOR gate that allows a 1-bit full adder to be implemented within an LC. In addition, a dedicated AND gate improves the efficiency of multiplier implementation.

The dedicated carry path can also be used to cascade function generators for implementing wide logic functions.

BUFTs

Each Spartan-II FPGA CLB contains two 3-state drivers (BUFTs) that can drive on-chip busses. See "Dedicated Routing," page 12. Each Spartan-II FPGA BUFT has an independent 3-state control pin and an independent input pin.

Block RAM

Spartan-II FPGAs incorporate several large block RAM memories. These complement the distributed RAM Look-Up Tables (LUTs) that provide shallow memory structures implemented in CLBs.

Block RAM memory blocks are organized in columns. All Spartan-II devices contain two such columns, one along each vertical edge. These columns extend the full height of the chip. Each memory block is four CLBs high, and consequently, a Spartan-II device eight CLBs high will contain two memory blocks per column, and a total of four blocks.

Table 5: Spartan-II Block RAM Amounts

Spartan-II Device	# of Blocks	Total Block RAM Bits
XC2S15	4	16K
XC2S30	6	24K
XC2S50	8	32K
XC2S100	10	40K
XC2S150	12	48K
XC2S200	14	56K

Each block RAM cell, as illustrated in Figure 5, is a fully synchronous dual-ported 4096-bit RAM with independent control signals for each port. The data widths of the two ports can be configured independently, providing built-in bus-width conversion.



Figure 5: Dual-Port Block RAM

Table 6 shows the depth and width aspect ratios for the block RAM.

Table	6 [.]	Block	RAM	Port	Aspect	Ratios
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Width	Depth	ADDR Bus	Data Bus
1	4096	ADDR<11:0>	DATA<0>
2	2048	ADDR<10:0>	DATA<1:0>
4	1024	ADDR<9:0>	DATA<3:0>
8	512	ADDR<8:0>	DATA<7:0>
16	256	ADDR<7:0>	DATA<15:0>

The Spartan-II FPGA block RAM also includes dedicated routing to provide an efficient interface with both CLBs and other block RAMs.

Programmable Routing Matrix

It is the longest delay path that limits the speed of any worst-case design. Consequently, the Spartan-II routing architecture and its place-and-route software were defined in a single optimization process. This joint optimization minimizes long-path delays, and consequently, yields the best system performance.

The joint optimization also reduces design compilation times because the architecture is software-friendly. Design cycles are correspondingly reduced due to shorter design iteration times.

Signals

There are two kinds of pins that are used to configure Spartan-II devices: Dedicated pins perform only specific configuration-related functions; the other pins can serve as general purpose I/Os once user operation has begun.

The dedicated pins comprise the mode pins (M2, M1, M0), the configuration clock pin (CCLK), the PROGRAM pin, the DONE pin and the boundary-scan pins (TDI, TDO, TMS, TCK). Depending on the selected configuration mode, CCLK may be an output generated by the FPGA, or may be generated externally, and provided to the FPGA as an input.

Note that some configuration pins can act as outputs. For correct operation, these pins require a V_{CCO} of 3.3V to drive an LVTTL signal or 2.5V to drive an LVCMOS signal. All the relevant pins fall in banks 2 or 3. The $\overline{\text{CS}}$ and $\overline{\text{WRITE}}$ pins for Slave Parallel mode are located in bank 1.

For a more detailed description than that given below, see "Pinout Tables" in Module 4 and XAPP176, Spartan-II FPGA Series Configuration and Readback.

The Process

The sequence of steps necessary to configure Spartan-II devices are shown in Figure 11. The overall flow can be divided into three different phases.

- Initiating Configuration
- Configuration memory clear
- Loading data frames
- Start-up

The memory clearing and start-up phases are the same for all configuration modes; however, the steps for the loading of data frames are different. Thus, the details for data frame loading are described separately in the sections devoted to each mode.

Initiating Configuration

There are two different ways to initiate the configuration process: applying power to the device or asserting the PROGRAM input.

Configuration on power-up occurs automatically unless it is delayed by the user, as described in a separate section below. The waveform for configuration on power-up is shown in Figure 12, page 19. Before configuration can begin, V_{CCO} Bank 2 must be greater than 1.0V. Furthermore, all V_{CCINT} power pins must be connected to a 2.5V supply. For more information on delaying configuration, see "Clearing Configuration Memory," page 19.

Once in user operation, the device can be re-configured simply by pulling the PROGRAM pin Low. The device acknowledges the beginning of the configuration process

by driving DONE Low, then enters the memory-clearing phase.



Figure 11: Configuration Flow Diagram



Notes: (referring to waveform above:)

1. Before configuration can begin, V_{CCINT} must be greater than 1.6V and V_{CCO} Bank 2 must be greater than 1.0V.

Figure 12: Configuration Timing on Power-Up

Clearing Configuration Memory

The device indicates that clearing the configuration memory is in progress by driving INIT Low. At this time, the user can delay configuration by holding either PROGRAM or INIT Low, which causes the device to remain in the memory clearing phase. Note that the bidirectional INIT line is driving a Low logic level during memory clearing. To avoid contention, use an open-drain driver to keep INIT Low.

With no delay in force, the device indicates that the memory is completely clear by driving INIT High. The FPGA samples its mode pins on this Low-to-High transition.

Loading Configuration Data

Once INIT is High, the user can begin loading configuration data frames into the device. The details of loading the configuration data are discussed in the sections treating the configuration modes individually. The sequence of operations necessary to load configuration data using the serial modes is shown in Figure 14. Loading data using the Slave Parallel mode is shown in Figure 19, page 25.

CRC Error Checking

During the loading of configuration data, a CRC value embedded in the configuration file is checked against a CRC value calculated within the FPGA. If the CRC values do not match, the FPGA drives INIT Low to indicate that a frame error has occurred and configuration is aborted.

To reconfigure the device, the PROGRAM pin should be asserted to reset the configuration logic. Recycling power also resets the FPGA for configuration. See "Clearing Configuration Memory".

Start-up

The start-up sequence oversees the transition of the FPGA from the configuration state to full user operation. A match of CRC values, indicating a successful loading of the configuration data, initiates the sequence.

During start-up, the device performs four operations:

- 1. The assertion of DONE. The failure of DONE to go High may indicate the unsuccessful loading of configuration data.
- 2. The release of the Global Three State net. This activates I/Os to which signals are assigned. The remaining I/Os stay in a high-impedance state with internal weak pull-down resistors present.
- 3. Negates Global Set Reset (GSR). This allows all flip-flops to change state.
- 4. The assertion of Global Write Enable (GWE). This allows all RAMs and flip-flops to change state.



Figure 18: Slave Parallel Configuration Circuit Diagram

Multiple Spartan-II FPGAs can be configured using the Slave Parallel mode, and be made to start-up simultaneously. To configure multiple devices in this way, wire the individual CCLK, Data, WRITE, and BUSY pins of all the devices in parallel. The individual devices are loaded separately by asserting the CS pin of each device in turn and writing the appropriate data. Sync-to-DONE start-up timing is used to ensure that the start-up sequence does not begin until all the FPGAs have been loaded. See "Start-up," page 19.

Write

When using the Slave Parallel Mode, write operations send packets of byte-wide configuration data into the FPGA. Figure 19, page 25 shows a flowchart of the write sequence used to load data into the Spartan-II FPGA. This is an expansion of the "Load Configuration Data Frames" block in Figure 11, page 18. The timing for write operations is shown in Figure 20, page 26. For the present example, the user holds $\overline{\text{WRITE}}$ and $\overline{\text{CS}}$ Low throughout the sequence of write operations. Note that when $\overline{\text{CS}}$ is asserted on successive CCLKs, $\overline{\text{WRITE}}$ must remain either asserted or de-asserted. Otherwise an abort will be initiated, as in the next section.

- 1. Drive data onto D0-D7. Note that to avoid contention, the data source should not be enabled while \overline{CS} is Low and \overline{WRITE} is High. Similarly, while \overline{WRITE} is High, no more than one device's \overline{CS} should be asserted.
- 2. On the rising edge of CCLK: If BUSY is Low, the data is accepted on this clock. If BUSY is High (from a previous write), the data is not accepted. Acceptance will instead occur on the first clock after BUSY goes Low, and the data must be held until this happens.
- 3. Repeat steps 1 and 2 until all the data has been sent.
- 4. De-assert $\overline{\text{CS}}$ and $\overline{\text{WRITE}}$.

Using Block RAM Features

The Spartan-II FPGA family provides dedicated blocks of on-chip, true dual-read/write port synchronous RAM, with 4096 memory cells. Each port of the block RAM memory can be independently configured as a read/write port, a read port, a write port, and can be configured to a specific data width. The block RAM memory offers new capabilities allowing the FPGA designer to simplify designs.

Operating Modes

Block RAM memory supports two operating modes.

- Read Through
- Write Back

Read Through (One Clock Edge)

The read address is registered on the read port clock edge and data appears on the output after the RAM access time. Some memories may place the latch/register at the outputs depending on the desire to have a faster clock-to-out versus setup time. This is generally considered to be an inferior solution since it changes the read operation to an asynchronous function with the possibility of missing an address/control line transition during the generation of the read pulse clock.

Write Back (One Clock Edge)

The write address is registered on the write port clock edge and the data input is written to the memory and mirrored on the write port input.

Block RAM Characteristics

- 1. All inputs are registered with the port clock and have a setup to clock timing specification.
- 2. All outputs have a read through or write back function depending on the state of the port WE pin. The outputs relative to the port clock are available after the clock-to-out timing specification.
- 3. The block RAM are true SRAM memories and do not have a combinatorial path from the address to the output. The LUT cells in the CLBs are still available with this function.
- 4. The ports are completely independent from each other (*i.e.*, clocking, control, address, read/write function, and data width) without arbitration.
- 5. A write operation requires only one clock edge.
- 6. A read operation requires only one clock edge.

The output ports are latched with a self timed circuit to guarantee a glitch free read. The state of the output port will not change until the port executes another read or write operation.

Library Primitives

Figure 31 and Figure 32 show the two generic library block RAM primitives. Table 11 describes all of the available primitives for synthesis and simulation.



DS001_31_061200





DS001_32_061200

Figure 32: Single-Port Block RAM Memory

Table 11: Available Library Primitives

Primitive	Port A Width	Port B Width
RAMB4_S1	1	N/A
RAMB4_S1_S1		1
RAMB4_S1_S2		2
RAMB4_S1_S4		4
RAMB4_S1_S8		8
RAMB4_S1_S16		16
RAMB4_S2	2	N/A
RAMB4_S2_S2		2
RAMB4_S2_S4		4
RAMB4_S2_S8		8
RAMB4_S2_S16		16

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СТТ

A sample circuit illustrating a valid termination technique for CTT appear in Figure 51. DC voltage specifications appear in Table 29 for the CTT standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics .



Figure 51: Terminated CTT

Table 29: CTT Voltage Specifications

Parameter	Min	Тур	Max
V _{CCO}	2.05 ⁽¹⁾	3.3	3.6
V _{REF}	1.35	1.5	1.65
V _{TT}	1.35	1.5	1.65
$V_{IH} \ge V_{REF} + 0.2$	1.55	1.7	-
$V_{IL} \leq V_{REF} - 0.2$	-	1.3	1.45
$V_{OH} \ge V_{REF} + 0.4$	1.75	1.9	-
$V_{OL} \leq V_{REF} - 0.4$	-	1.1	1.25
I _{OH} at V _{OH} (mA)	-8	-	-
I _{OL} at V _{OL} (mA)	8	-	-

Notes:

1. Timing delays are calculated based on V_{CCO} min of 3.0V.

PCI33_3 and PCI66_3

PCI33_3 or PCI66_3 require no termination. DC voltage specifications appear in Table 30 for the PCI33_3 and PCI66_3 standards. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

Table 30: PCI33_3 and PCI66_3 Voltage Specifications

Parameter	Min	Тур	Max
V _{CCO}	3.0	3.3	3.6
V _{REF}	-	-	-
V _{TT}	-	-	-
$V_{IH} = 0.5 \times V_{CCO}$	1.5	1.65	V _{CCO} + 0.5
$V_{IL} = 0.3 \times V_{CCO}$	-0.5	0.99	1.08
$V_{OH} = 0.9 \times V_{CCO}$	2.7	-	-
$V_{OL} = 0.1 \times V_{CCO}$	-	-	0.36
I _{OH} at V _{OH} (mA)	Note 1	-	-
I _{OL} at V _{OL} (mA)	Note 1	-	-

Notes:

1. Tested according to the relevant specification.

PCI33_5

PCI33_5 requires no termination. DC voltage specifications appear in Table 31 for the PCI33_5 standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

Table 31: PCI33_5 Voltage Specifications

Parameter	Min	Тур	Max
V _{CCO}	3.0	3.3	3.6
V _{REF}	-	-	-
V _{TT}	-	-	-
V _{IH}	1.425	1.5	5.5
V _{IL}	-0.5	1.0	1.05
V _{OH}	2.4	-	-
V _{OL}	-	-	0.55
I _{OH} at V _{OH} (mA)	Note 1	-	-
I _{OL} at V _{OL} (mA)	Note 1	-	-

Notes:

1. Tested according to the relevant specification.

IOB Output Switching Characteristics

Output delays terminating at a pad are specified for LVTTL with 12 mA drive and fast slew rate. For other standards, adjust the delays with the values shown in "IOB Output Delay Adjustments for Different Standards," page 59.

		Speed Grade				
		-6		-5		
Symbol	Description	Min	Max	Min	Max	Units
Propagation Delays	5					
T _{IOOP}	O input to pad	-	2.9	-	3.4	ns
T _{IOOLP}	O input to pad via transparent latch	-	3.4	-	4.0	ns
3-state Delays		1				
T _{IOTHZ}	T input to pad high-impedance ⁽¹⁾	-	2.0	-	2.3	ns
T _{IOTON}	T input to valid data on pad	-	3.0	-	3.6	ns
T _{IOTLPHZ}	T input to pad high impedance via transparent latch ⁽¹⁾	-	2.5	-	2.9	ns
T _{IOTLPON}	T input to valid data on pad via transparent latch	-	3.5	-	4.2	ns
T _{GTS}	GTS to pad high impedance ⁽¹⁾	-	5.0	-	5.9	ns
Sequential Delays		1	L	1		
T _{IOCKP}	Clock CLK to pad	-	2.9	-	3.4	ns
Т _{ЮСКНZ}	Clock CLK to pad high impedance (synchronous) ⁽¹⁾	-	2.3	-	2.7	ns
T _{IOCKON}	Clock CLK to valid data on pad (synchronous)	-	3.3	-	4.0	ns
Setup/Hold Times	with Respect to Clock CLK ⁽²⁾	1	l.			
TIOOCK / TIOCKO	O input	1.1/0	-	1.3/0	-	ns
T _{IOOCECK} /	OCE input	0.9 / 0.01	-	0.9/0.01	-	ns
TIOCKOCE						
T _{IOSRCKO} /	SR input (OFF)	1.2/0	-	1.3 / 0	-	ns
TIOCKOSR				/ -		
TIOTCK / TIOCKT	3-state setup times, T input	0.8/0	-	0.9/0	-	ns
Т _{ІОТСЕСК} /	3-state setup times, TCE input	1.0/0	-	1.0/0	-	ns
		11/0		10/0		
	3-state setup times, SK input (TFF)	1.170	-	1.2/0	-	ns
Set/Reset Delays						
	SR input to pad (asynchronous)	_	37	_	44	ns
	SR input to pad high impedance (asynchronous) ⁽¹⁾	-	3.1	-	37	ns
	SR input to valid data on pad (asynchronous)	-	4 1	-	49	ns
	GSR to pad	_	9.1	_	11 7	ns
' IOGSRQ	OUN ID Pau	-	9.9	-	11.7	115

Notes:

1. Three-state turn-off delays should not be adjusted.

2. A zero hold time listing indicates no hold time or a negative hold time.

Calculation of T_{IOOP} as a Function of Capacitance

 $T_{\rm IOOP}$ is the propagation delay from the O Input of the IOB to the pad. The values for $T_{\rm IOOP}$ are based on the standard capacitive load (C_{SL}) for each I/O standard as listed in the table "Constants for Calculating TIOOP", below.

For other capacitive loads, use the formulas below to calculate an adjusted propagation delay, T_{IOOP1} .

$$T_{IOOP1} = T_{IOOP} + Adj + (C_{LOAD} - C_{SL}) * F_{L}$$

Where:

Adj is selected from "IOB Output Delay Adjustments for Different Standards", page 59, according to the I/O standard used

 $C_{\text{LOAD}}\,$ is the capacitive load for the design

F_L is the capacitance scaling factor

Delay Measurement Methodology

Standard	V _L (1)	V _H (1)	Meas. Point	V _{REF} Typ ⁽²⁾
LVTTL	0	3	1.4	-
LVCMOS2	0	2.5	1.125	-
PCI33_5	Pe	r PCI Spec		-
PCI33_3	Pe	r PCI Spec		-
PCI66_3	Pe	-		
GTL	V _{REF} – 0.2	V _{REF} + 0.2	V_{REF}	0.80
GTL+	V _{REF} – 0.2	V _{REF} + 0.2	V_{REF}	1.0
HSTL Class I	V _{REF} – 0.5	V _{REF} + 0.5	V_{REF}	0.75
HSTL Class III	V _{REF} – 0.5	V _{REF} + 0.5	V_{REF}	0.90
HSTL Class IV	V _{REF} – 0.5	V _{REF} + 0.5	V_{REF}	0.90
SSTL3 I and II	V _{REF} – 1.0	V _{REF} + 1.0	V_{REF}	1.5
SSTL2 I and II	$V_{REF} - 0.75$	V _{REF} + 0.75	V_{REF}	1.25
CTT	V _{REF} – 0.2	V _{REF} + 0.2	V_{REF}	1.5
AGP	V _{REF} – (0.2xV _{CCO})	V _{REF} + (0.2xV _{CCO})	V _{REF}	Per AGP Spec

Notes:

- 1. Input waveform switches between V_L and V_H.
- 2. Measurements are made at V_{REF} Typ, Maximum, and Minimum. Worst-case values are reported.
- I/O parameter measurements are made with the capacitance values shown in the table, "Constants for Calculating TIOOP". See Xilinx application note <u>XAPP179</u> for the appropriate terminations.
- 4. I/O standard measurements are reflected in the IBIS model information except where the IBIS format precludes it.

Constants for Calculating T_{IOOP}

Standard	C _{SL} ⁽¹⁾ (pF)	F _L (ns/pF)
LVTTL Fast Slew Rate, 2 mA drive	35	0.41
LVTTL Fast Slew Rate, 4 mA drive	35	0.20
LVTTL Fast Slew Rate, 6 mA drive	35	0.13
LVTTL Fast Slew Rate, 8 mA drive	35	0.079
LVTTL Fast Slew Rate, 12 mA drive	35	0.044
LVTTL Fast Slew Rate, 16 mA drive	35	0.043
LVTTL Fast Slew Rate, 24 mA drive	35	0.033
LVTTL Slow Slew Rate, 2 mA drive	35	0.41
LVTTL Slow Slew Rate, 4 mA drive	35	0.20
LVTTL Slow Slew Rate, 6 mA drive	35	0.100
LVTTL Slow Slew Rate, 8 mA drive	35	0.086
LVTTL Slow Slew Rate, 12 mA drive	35	0.058
LVTTL Slow Slew Rate, 16 mA drive	35	0.050
LVTTL Slow Slew Rate, 24 mA drive	35	0.048
LVCMOS2	35	0.041
PCI 33 MHz 5V	50	0.050
PCI 33 MHZ 3.3V	10	0.050
PCI 66 MHz 3.3V	10	0.033
GTL	0	0.014
GTL+	0	0.017
HSTL Class I	20	0.022
HSTL Class III	20	0.016
HSTL Class IV	20	0.014
SSTL2 Class I	30	0.028
SSTL2 Class II	30	0.016
SSTL3 Class I	30	0.029
SSTL3 Class II	30	0.016
СТТ	20	0.035
AGP	10	0.037

Notes:

- 1. I/O parameter measurements are made with the capacitance values shown above. See Xilinx application note <u>XAPP179</u> for the appropriate terminations.
- 2. I/O standard measurements are reflected in the IBIS model information except where the IBIS format precludes it.

CLB Switching Characteristics

Delays originating at F/G inputs vary slightly according to the input used. The values listed below are worst-case. Precise values are provided by the timing analyzer.

		Speed Grade				
		-6 -5		5		
Symbol	Description	Min	Max	Min	Max	Units
Combinatorial Dela	ays	· · · · · · · · · · · · · · · · · · ·				
T _{ILO}	4-input function: F/G inputs to X/Y outputs	-	0.6	-	0.7	ns
T _{IF5}	5-input function: F/G inputs to F5 output	-	0.7	-	0.9	ns
T _{IF5X}	5-input function: F/G inputs to X output	-	0.9	-	1.1	ns
T _{IF6Y}	6-input function: F/G inputs to Y output via F6 MUX	-	1.0	-	1.1	ns
T _{F5INY}	6-input function: F5IN input to Y output	-	0.4	-	0.4	ns
T _{IFNCTL}	Incremental delay routing through transparent latch to XQ/YQ outputs	-	0.7	-	0.9	ns
T _{BYYB}	BY input to YB output	-	0.6	-	0.7	ns
Sequential Delays				<u> </u>		
т _{ско}	FF clock CLK to XQ/YQ outputs	-	1.1	-	1.3	ns
T _{CKLO}	Latch clock CLK to XQ/YQ outputs	-	1.2	-	1.5	ns
Setup/Hold Times	with Respect to Clock CLK ⁽¹⁾			<u> </u>		
T _{ICK} / T _{CKI}	4-input function: F/G inputs	1.3/0	-	1.4 / 0	-	ns
T _{IF5CK} / T _{CKIF5}	5-input function: F/G inputs	1.6 / 0	-	1.8 / 0	-	ns
T _{F5INCK} / T _{CKF5IN}	6-input function: F5IN input	1.0/0	-	1.1/0	-	ns
T _{IF6CK} / T _{CKIF6}	6-input function: F/G inputs via F6 MUX	1.6 / 0	-	1.8 / 0	-	ns
T _{DICK} / T _{CKDI}	BX/BY inputs	0.8/0	-	0.8/0	-	ns
T _{CECK} / T _{CKCE}	CE input	0.9/0	-	0.9/0	-	ns
T _{RCK} / T _{CKR}	SR/BY inputs (synchronous)	0.8/0	-	0.8/0	-	ns
Clock CLK						
T _{CH}	Minimum pulse width, High	-	1.9	-	1.9	ns
T _{CL}	Minimum pulse width, Low	-	1.9	-	1.9	ns
Set/Reset		II				
T _{RPW}	Minimum pulse width, SR/BY inputs	3.1	-	3.1	-	ns
T _{RQ}	Delay from SR/BY inputs to XQ/YQ outputs (asynchronous)	-	1.1	-	1.3	ns
T _{IOGSRQ}	Delay from GSR to XQ/YQ outputs	-	9.9	-	11.7	ns
F _{TOG}	Toggle frequency (for export control)	-	263	-	263	MHz

Notes:

1. A zero hold time listing indicates no hold time or a negative hold time.

IOB Input Delay Adjustments for Different Standards ⁽¹⁾

Input delays associated with the pad are specified for LVTTL. For other standards, adjust the delays by the values shown. A delay adjusted in this way constitutes a worst-case limit.

			Speed Grade				
Symbol	Description	Standard	-6	-5	Units		
Data Input D	Data Input Delay Adjustments						
T _{ILVTTL}	Standard-specific data input delay adjustments	LVTTL	0	0	ns		
T _{ILVCMOS2}		LVCMOS2	0 .04	0 .05	ns		
T _{IPCI333}		PCI,33 MHz3.3V	θ.11	0 .13	ns		
T _{IPCI335}		PCI,33 MHz5.0V	0.26	0.30	ns		
T _{IPCI6}		PCI,6MHz3.3V	0 .11 €).13	ns		
T _{IGTL}		GTL	0.20	0.24	ns		
T _{IGTLP}		GTL+	0.11	0.13	ns		
T _{IHSTL}		HSTL	0.03	0.04	ns		
T _{ISSTL2}		SSTL2	0 .08	0 .09	ns		
T _{ISSTL3}		SSTL3	0 .04	0 .05	ns		
T _{ICTT}		СТТ	0.02	0.02	ns		
T _{IAGP}		AGP	0 .06	0 .07	ns		

Notes:

1. Input timing for LVTTL is measured at 1.4V. For other I/O standards, see the talkate Measurement Methodology, page θ.

Calculation of T $_{\rm IOOP}$ as a Function of Capacitance

 T_{IOOP} is the propagation delay from the O Input of the IOB to the pad. The values for $_{I\overline{D}OP}$ are based on the standard capacitive load (G_L) for each I/O standard as listed in the table Constants for Calculating TIOOF, below.

For other capacitive loads, use the formulas below to calculate an adjusted propagation delay, \mathcal{F}_{OP1} .

 $T_{IOOP1} = T_{IOOP} + Adj + (C_{LOAD} - C_{SL}) * F_L$

Where:

Adj is selected from IOB Output Delay Adjustments for Different Standard, grage 59, according to the I/O standard used

CLOAD is the capacitive load for the design

F_L is the capacitance scaling factor

Delay Measurement Methodology

Standard	V L ⁽¹⁾	V _H ⁽¹⁾	Meas. Point	V _{REF} Typ ⁽²⁾
LVTTL	0	3	1.4	-
LVCMOS2	0	2.5	1.125	-
PCI33 <u>5</u>	Per PCI Spec		-	
PCI33 <u>3</u>	Per PCI Spec		-	
PCI <u>6</u>	Pe	r PCI Spec		-
GTL	V _{REF} -0.2	V _{REF} + 0.2	V _{REF}	0.80
GTL+	V _{REF} -0.2	V _{REF} + 0.2	V _{REF}	1.0
HSTL Class I	V _{REF} -0.5	V _{REF} + 0.5	V _{REF}	0.75
HSTL Class III	V _{REF} -0.5	V _{REF} + 0.5	V _{REF}	0.90
HSTL Class IV	V _{REF} -0.5	V _{REF} + 0.5	V _{REF}	0.90
SSTL3 I and II	V _{REF} -1.0	V _{REF} + 1.0	V _{REF}	1.5
SSTL2 I and II	V _{REF} – 0.75	$V_{REF} + 0.75$	V _{REF}	1.25
CTT	V _{REF} -0.2	V _{REF} + 0.2	V _{REF}	1.5
AGP	V _{REF} – (0.2xV _{CCO})	V _{REF} + (0.2xV _{CCO})	V _{REF}	Per AGP Spec

Notes:

1. Input waveform switches between Vand V_H.

 I/O parameter measurements are made with the capacitance values shown in the tabl@onstants for Calculating TIOOP." See Xilinx application note XAPP17for the appropriate terminations.

4. I/O standard measurements are reflected in the IBIS model information except where the IBIS format precludes it.

Constants for Calculating T IOOP

Standard	C _{SL} ⁽¹⁾ (pF)	F _L (ns/pF)
LVTTL Fast Slew Rate,2 mA drive	35	0.41
LVTTL Fast Slew Rate,4 mA drive	35	0.20
LVTTL Fast Slew Rate,6mA drive	35	0.13
LVTTL Fast Slew Rate,8 mA drive	35	0.079
LVTTL Fast Slew Rate,12 mA drive	35	0.044
LVTTL Fast Slew Rate,16nA drive	35	0.043
LVTTL Fast Slew Rate,24 mA drive	35	0.033
LVTTL Slow Slew Rate,2 mA drive	35	0.41
LVTTL Slow Slew Rate,4 mA drive	35	0.20
LVTTL Slow Slew Rate, @nA drive	35	0.100
LVTTL Slow Slew Rate,8 mA drive	35	0.086
LVTTL Slow Slew Rate, 12 mA drive	35	0.058
LVTTL Slow Slew Rate,16mA drive	35	0.050
LVTTL Slow Slew Rate,24 mA drive	35	0.048
LVCMOS2	35	0.041
PCI 33 MHz5V	50	0.050
PCI 33 MHZ3.3V	10	0.050
PCI 6MHz3.3V	10	0.033
GTL	0	0.014
GTL+	0	0.017
HSTL Class I	20	0.022
HSTL Class III	20	0.016
HSTL Class IV	20	0.014
SSTL2 Class I	30	0.028
SSTL2 Class II	30	0.016
SSTL3 Class I	30	0.029
SSTL3 Class II	30	0.016
СТТ	20	0.035
AGP	10	0.037

Notes:

- 1. I/O parameter measurements are made with the capacitance values shown above. See Xilinx application not propriate terminations.
- 2. I/O standard measurements are reflected in the IBIS model information except where the IBIS format precludes it.

Measurements are made at K_{EF} Typ,Maximum,and Minimum. Worst-case values are reported.